


## "High Side Chopper" IGBT SOT-227 (Trench IGBT), 100 A


**SOT-227**
**FEATURES**

- Trench IGBT technology
- Very low  $V_{CE(on)}$
- Square RBSOA
- HEXFRED® clamping diode
- 10  $\mu$ s short circuit capability
- Fully isolated package
- Speed 4 kHz to 30 kHz
- Very low internal inductance ( $\leq 5$  nH typical)
- Industry standard outline
- UL approved file E78996 
- Compliant to RoHS directive 2002/95/EC


**RoHS  
COMPLIANT**
**PRODUCT SUMMARY**

$V_{CES}$	1200 V
$I_C$ DC	100 A at 71 °C
$V_{CE(on)}$ typical at 100 A, 25 °C	2.36 V

**BENEFITS**

- Designed for increased operating efficiency in power conversion: UPS, SMPS, welding, induction heating
- Easy to assemble and parallel
- Direct mounting on heatsink
- Plug-in compatible with other SOT-227 packages
- Low EMI, requires less snubbing

**ABSOLUTE MAXIMUM RATINGS**

PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS
Collector to emitter voltage	$V_{CES}$		1200	V
Continuous collector current	$I_C$	$T_C = 25\text{ °C}$	134	A
		$T_C = 80\text{ °C}$	92	
Pulsed collector current	$I_{CM}$		270	
Clamped inductive load current	$I_{LM}$		270	
Diode continuous forward current	$I_F$	$T_C = 25\text{ °C}$	87	
		$T_C = 80\text{ °C}$	59	
Gate to emitter voltage	$V_{GE}$		$\pm 20$	V
Power dissipation, IGBT	$P_D$	$T_C = 25\text{ °C}$	463	W
		$T_C = 80\text{ °C}$	260	
Power dissipation, diode	$P_D$	$T_C = 25\text{ °C}$	338	
		$T_C = 80\text{ °C}$	190	
RMS isolation voltage	$V_{ISOL}$	Any terminal to case, $t = 1$ min	2500	V

ELECTRICAL SPECIFICATIONS (T <sub>J</sub> = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Collector to emitter breakdown voltage	V <sub>BR(CES)</sub>	V <sub>GE</sub> = 0 V, I <sub>C</sub> = 1 mA	1200	-	-	
Collector to emitter voltage	V <sub>CE(on)</sub>	V <sub>GE</sub> = 15 V, I <sub>C</sub> = 50 A	-	1.79	2.33	V
		V <sub>GE</sub> = 15 V, I <sub>C</sub> = 100 A	-	2.36	2.85	
		V <sub>GE</sub> = 15 V, I <sub>C</sub> = 50 A, T <sub>J</sub> = 125 °C	-	2.05	2.62	
		V <sub>GE</sub> = 15 V, I <sub>C</sub> = 100 A, T <sub>J</sub> = 125 °C	-	2.8	3.42	
Gate threshold voltage	V <sub>GE(th)</sub>	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 500 μA	5	5.8	7	
Temperature coefficient of threshold voltage	V <sub>GE(th)</sub> /ΔT <sub>J</sub>	V <sub>CE</sub> = V <sub>GE</sub> , I <sub>C</sub> = 1 mA (25 °C to 125 °C)	-	- 15.6	-	mV/°C
Collector to emitter leakage current	I <sub>CES</sub>	V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 1200 V	-	0.5	100	μA
		V <sub>GE</sub> = 0 V, V <sub>CE</sub> = 1200 V, T <sub>J</sub> = 125 °C	-	0.052	2	mA
Diode reverse breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 1 mA	1200	-	-	V
Diode forward voltage drop	V <sub>FM</sub>	I <sub>C</sub> = 50 A, V <sub>GE</sub> = 0 V	-	2.53	3.55	V
		I <sub>C</sub> = 100 A, V <sub>GE</sub> = 0 V	-	3.32	4.35	
		I <sub>C</sub> = 50 A, V <sub>GE</sub> = 0 V, T <sub>J</sub> = 125 °C	-	2.66	3.70	
		I <sub>C</sub> = 100 A, V <sub>GE</sub> = 0 V, T <sub>J</sub> = 125 °C	-	3.7	4.50	
Diode reverse leakage current	I <sub>RM</sub>	V <sub>R</sub> = V <sub>R</sub> rated	-	4	50	μA
		T <sub>J</sub> = 125 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	0.6	3	mA
Gate to emitter leakage current	I <sub>GES</sub>	V <sub>GE</sub> = ± 20 V	-	-	± 200	nA

SWITCHING CHARACTERISTICS (T <sub>J</sub> = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Total gate charge (turn-on)	Q <sub>g</sub>	I <sub>C</sub> = 100 A, V <sub>CC</sub> = 600 V, V <sub>GE</sub> = 15 V	-	400	-	nC	
Gate to emitter charge (turn-on)	Q <sub>ge</sub>		-	120	-		
Gate to collector charge (turn-on)	Q <sub>gc</sub>		-	170	-		
Turn-on switching loss	E <sub>on</sub>	I <sub>C</sub> = 100 A, V <sub>CC</sub> = 600 V, V <sub>GE</sub> = 15 V, R <sub>g</sub> = 5 Ω, L = 500 μH	-	21.9	-	mJ	
Turn-off switching loss	E <sub>off</sub>		-	5.48	-		
Total switching loss	E <sub>tot</sub>		-	27.38	-		
Turn-on switching loss	E <sub>on</sub>		I <sub>C</sub> = 100 A, V <sub>CC</sub> = 600 V, V <sub>GE</sub> = 15 V, R <sub>g</sub> = 5 Ω, L = 500 μH, T <sub>J</sub> = 125 °C	-	23.6		-
Turn-off switching loss	E <sub>off</sub>			-	7.65		-
Total switching loss	E <sub>tot</sub>			-	31.25		-
Turn-on delay time	t <sub>d(on)</sub>	Energy losses include tail and diode recovery (see fig. 18)		-	195	-	ns
Rise time	t <sub>r</sub>		-	259	-		
Turn-off delay time	t <sub>d(off)</sub>		-	188	-		
Fall time	t <sub>f</sub>		-	212	-		
Reverse bias safe operating area	RBSOA	T <sub>J</sub> = 150 °C, I <sub>C</sub> = 270 A, R <sub>g</sub> = 22 Ω, V <sub>GE</sub> = 15 V to 0 V, V <sub>CC</sub> = 900 V, V <sub>P</sub> = 1200 V	Fullsquare				
Short circuit safe operating area	SCSOA	T <sub>J</sub> = 150 °C, R <sub>g</sub> = 22 Ω, V <sub>GE</sub> = 15 V to 0 V, V <sub>CC</sub> = 900 V, V <sub>P</sub> = 1200 V	10			μs	
Diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 50 A, di/dt = 200 A/μs, V <sub>R</sub> = 200 V	-	129	161	ns	
Diode peak reverse current	I <sub>rr</sub>		-	11	14	A	
Diode recovery charge	Q <sub>rr</sub>		-	700	1046	nC	
Diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 50 A, di/dt = 200 A/μs, V <sub>R</sub> = 200 V, T <sub>J</sub> = 125 °C	-	208	257	ns	
Diode peak reverse current	I <sub>rr</sub>		-	17	21	A	
Diode recovery charge	Q <sub>rr</sub>		-	1768	2698	nC	



THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	$T_J, T_{Stg}$	- 40	-	150	$^{\circ}\text{C}$
Thermal resistance, junction to case	IGBT	-	-	0.27	$^{\circ}\text{C/W}$
	Diode	-	-	0.37	
Thermal resistance, case to sink per module	$R_{thCS}$	-	0.05	-	
Mounting torque, 6-32 or M3 screw		-	-	1.3	Nm
Weight		-	30	-	g

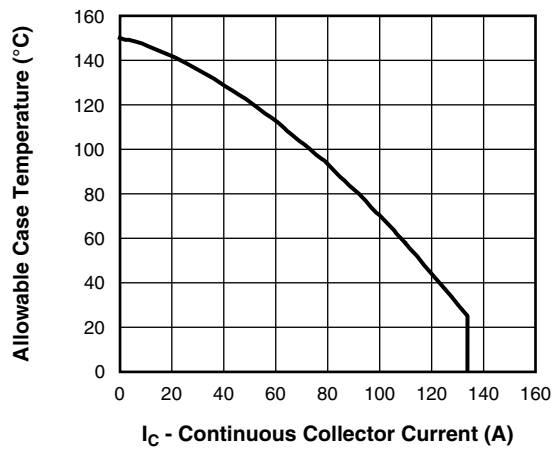


Fig. 1 - Maximum DC IGBT Collector Current vs. Case Temperature

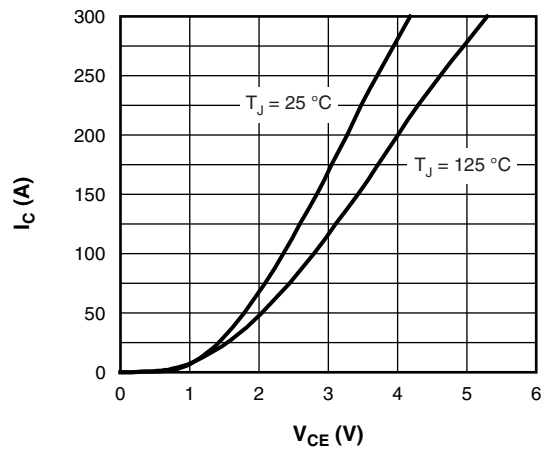


Fig. 3 - Typical IGBT Collector Current Characteristics

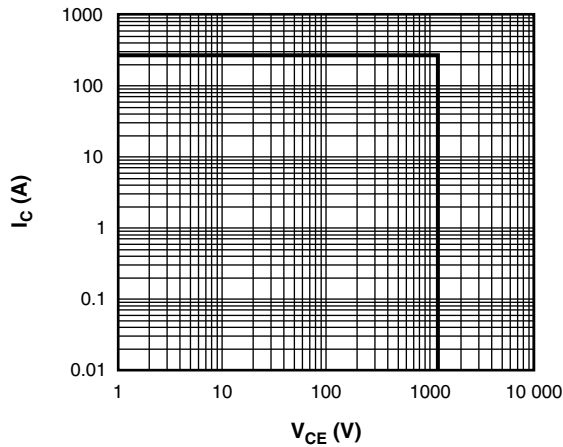


Fig. 2 - IGBT Reverse Bias SOA  
 $T_J = 150^{\circ}\text{C}, V_{GE} = 15\text{ V}$

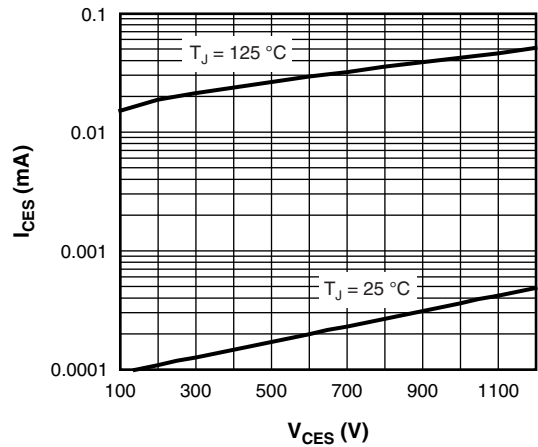


Fig. 4 - Typical IGBT Zero Gate Voltage Collector Current

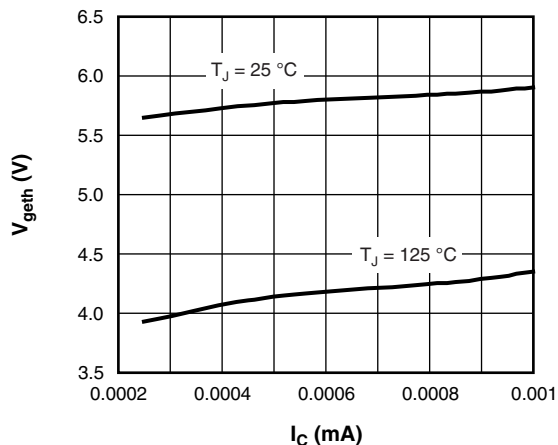


Fig. 5 - Typical IGBT Threshold Voltage

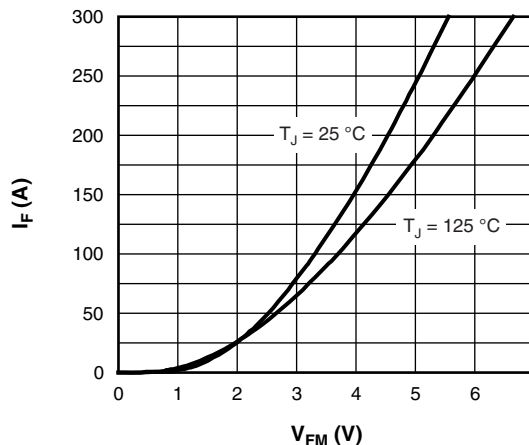


Fig. 8 - Typical Diode Forward Characteristics

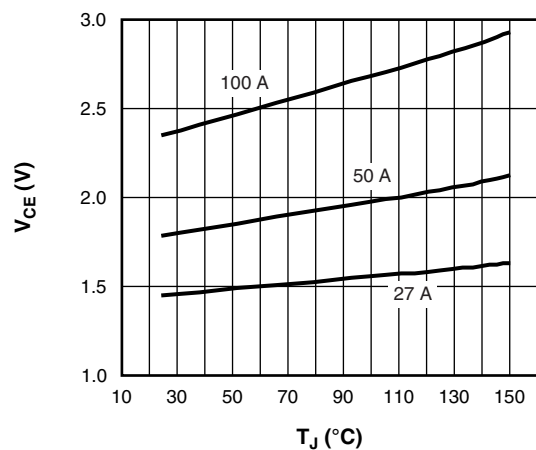


Fig. 6 - Typical IGBT Collector to Emitter Voltage vs. Junction Temperature,  $V_{GE} = 15\text{ V}$

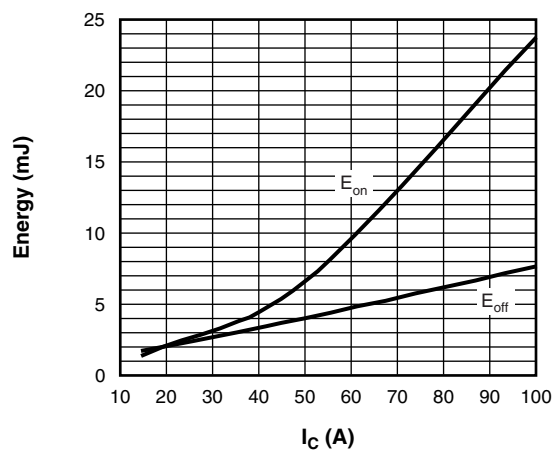


Fig. 9 - Typical IGBT Energy Loss vs.  $I_C$   
 $T_J = 125\text{ °C}$ ,  $L = 500\text{ }\mu\text{H}$ ,  $V_{CC} = 600\text{ V}$ ,  
 $R_g = 5\text{ }\Omega$ ,  $V_{GE} = 15\text{ V}$

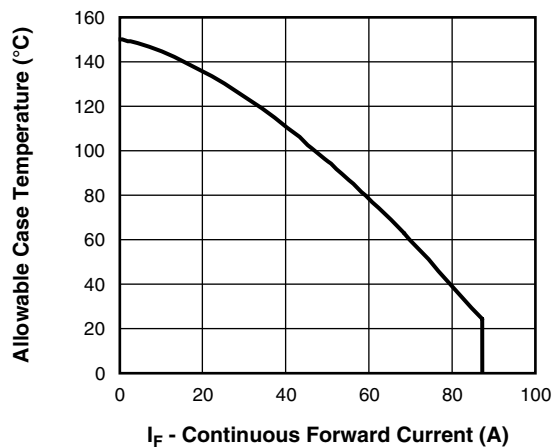


Fig. 7 - Maximum DC Forward Current vs. Case Temperature

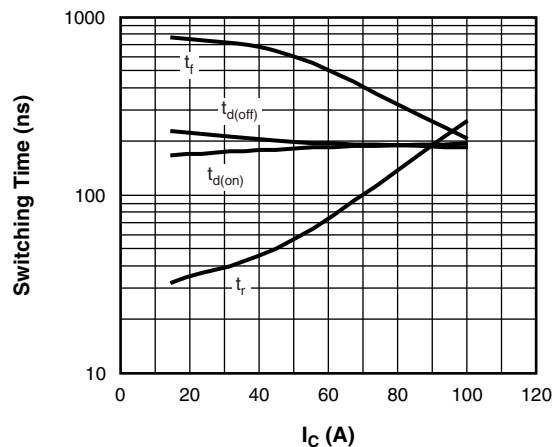


Fig. 10 - Typical IGBT Switching Time vs.  $I_C$   
 $T_J = 125\text{ °C}$ ,  $L = 500\text{ }\mu\text{H}$ ,  $V_{CC} = 600\text{ V}$ ,  
 $R_g = 5\text{ }\Omega$ ,  $V_{GE} = 15\text{ V}$

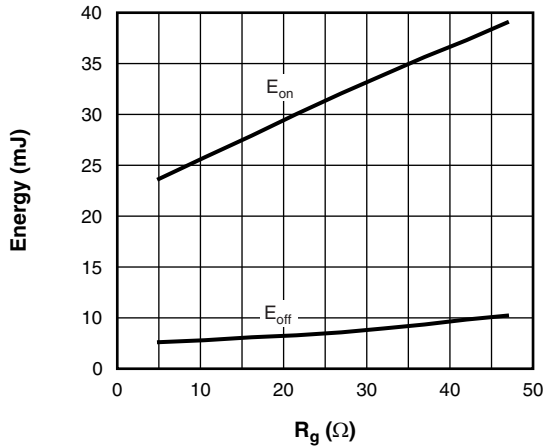


Fig. 11 - Typical IGBT Energy Loss vs.  $R_g$   
 $T_J = 125^\circ\text{C}$ ,  $I_C = 100\text{ A}$ ,  $L = 500\ \mu\text{H}$ ,  
 $V_{CC} = 600\text{ V}$ ,  $V_{GE} = 15\text{ V}$

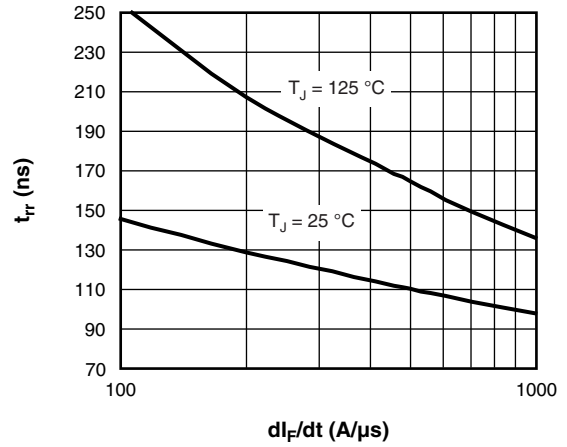


Fig. 13 - Typical  $t_{rr}$  Diode vs.  $dI_F/dt$   
 $V_R = 200\text{ V}$ ,  $I_F = 50\text{ A}$

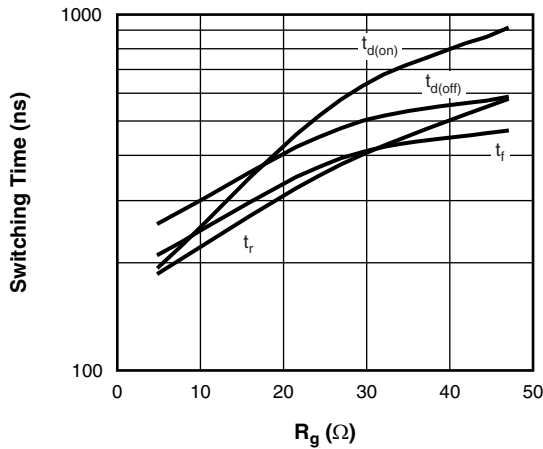


Fig. 12 - Typical IGBT Switching Time vs.  $R_g$   
 $T_J = 125^\circ\text{C}$ ,  $L = 500\ \mu\text{H}$ ,  $V_{CC} = 600\text{ V}$ ,  
 $I_C = 100\text{ A}$ ,  $V_{GE} = 15\text{ V}$

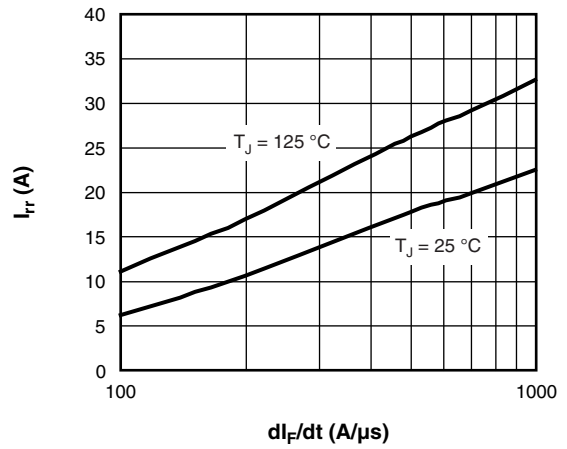


Fig. 14 - Typical  $I_{rr}$  Diode vs.  $dI_F/dt$   
 $V_R = 200\text{ V}$ ,  $I_F = 50\text{ A}$

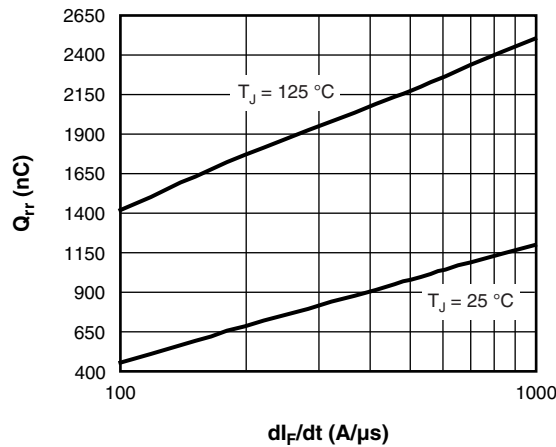


Fig. 15 - Typical  $Q_{rr}$  Diode vs.  $dI_F/dt$   
 $V_R = 200\text{ V}$ ,  $I_F = 50\text{ A}$

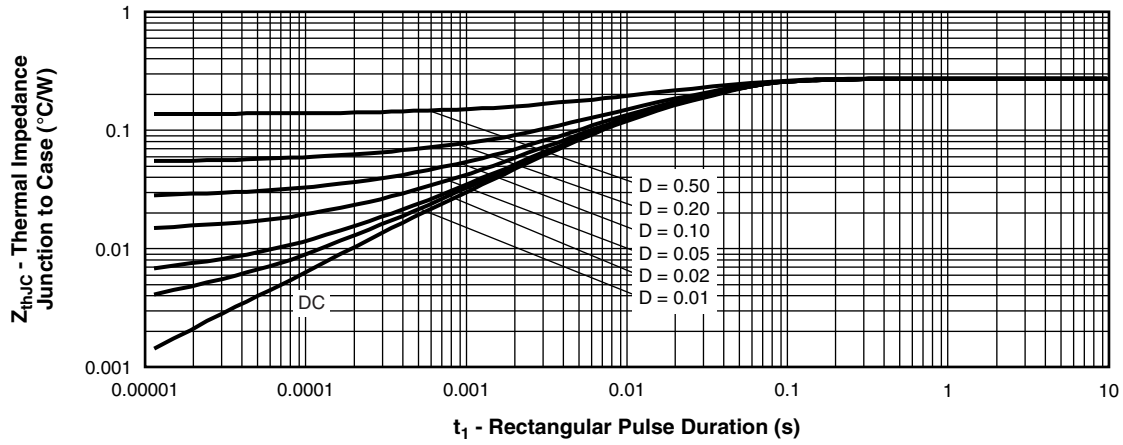


Fig. 16 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics (IGBT)

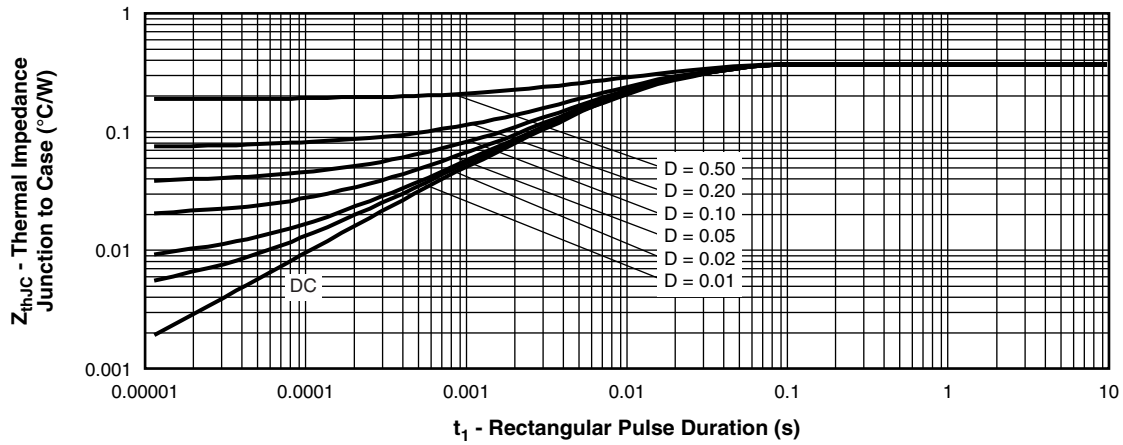
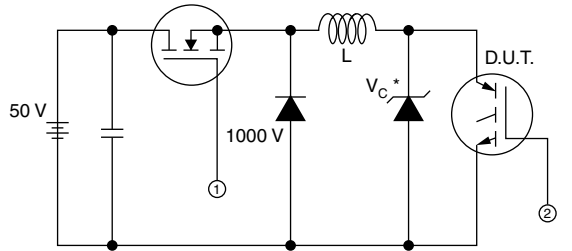


Fig. 17 - Maximum Thermal Impedance  $Z_{thJC}$  Characteristics (Diode)

## "High Side Chopper" IGBT SOT-227 Vishay Semiconductors (Trench IGBT), 100 A



\* Driver same type as D.U.T.;  $V_C = 80\% \text{ of } V_{ce(max)}$   
 \* Note: Due to the 50 V power supply, pulse width and inductor will increase to obtain  $I_d$

Fig. 18a - Clamped Inductive Load Test Circuit

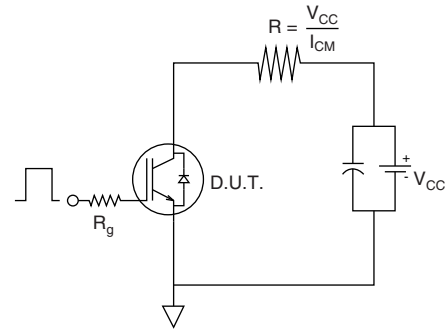


Fig. 18b - Pulsed Collector Current Test Circuit

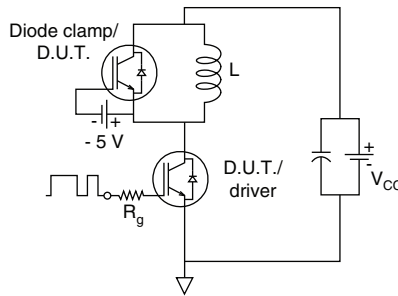


Fig. 19a - Switching Loss Test Circuit

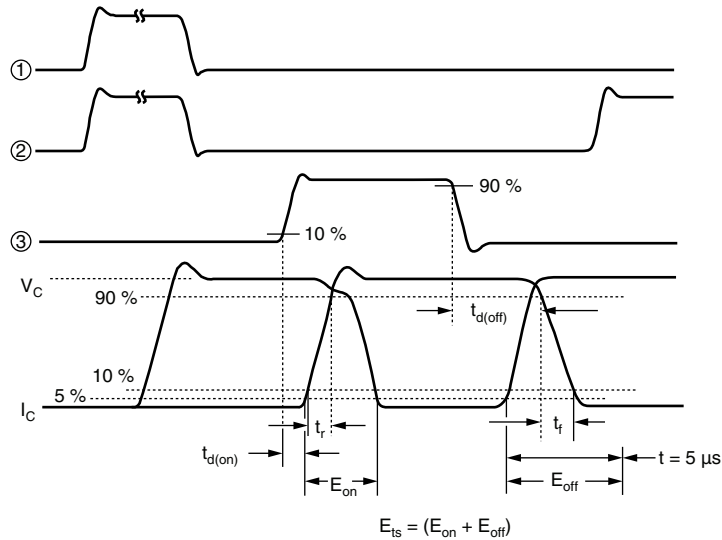


Fig. 19b - Switching Loss Waveforms Test Circuit

# GT100NA120UX



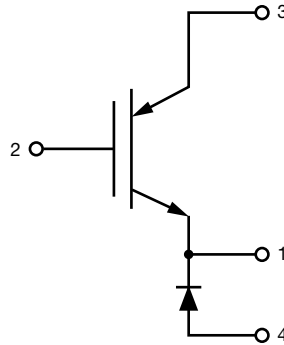
Vishay Semiconductors "High Side Chopper" IGBT SOT-227  
(Trench IGBT), 100 A

## ORDERING INFORMATION TABLE

Device code	<b>G</b>	<b>T</b>	<b>100</b>	<b>N</b>	<b>A</b>	<b>120</b>	<b>U</b>	<b>X</b>
	①	②	③	④	⑤	⑥	⑦	⑧

- 1** - Insulated Gate Bipolar Transistor (IGBT)
- 2** - T = Trench IGBT
- 3** - Current rating (100 = 100 A)
- 4** - Circuit configuration (N = High side chopper)
- 5** - Package indicator (A = SOT-227)
- 6** - Voltage rating (120 = 1200 V)
- 7** - Speed/type (U = Ultrafast IGBT)
- 8** - Diode (X = HEXFRED®)

## CIRCUIT CONFIGURATION

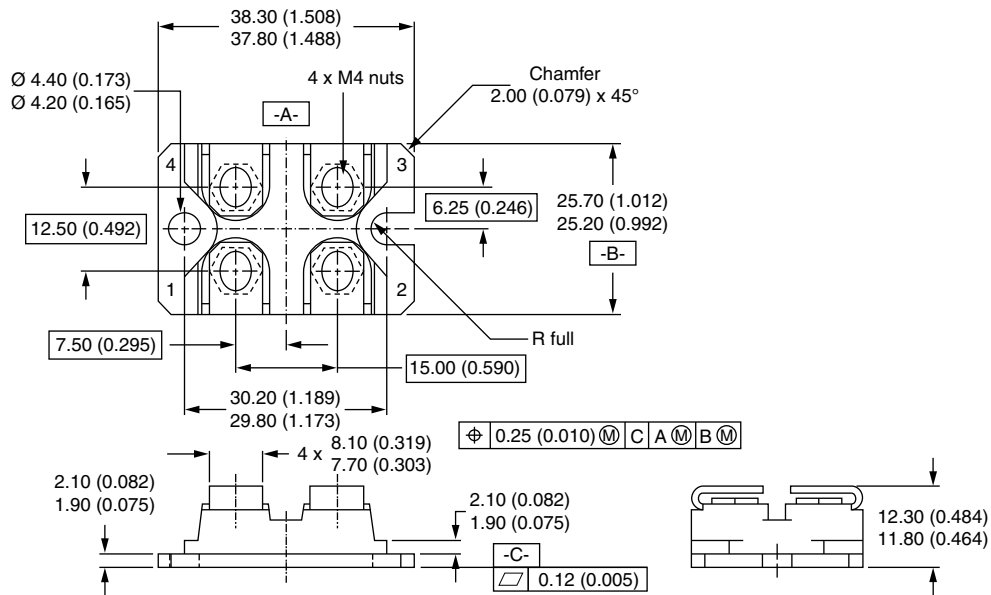


LINKS TO RELATED DOCUMENTS	
Dimensions	<a href="http://www.vishay.com/doc?95036">www.vishay.com/doc?95036</a>
Packaging information	<a href="http://www.vishay.com/doc?95037">www.vishay.com/doc?95037</a>



## SOT-227

**DIMENSIONS** in millimeters (inches)



**Notes**

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- Controlling dimension: millimeter



## Disclaimer

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